

# 2SK4093

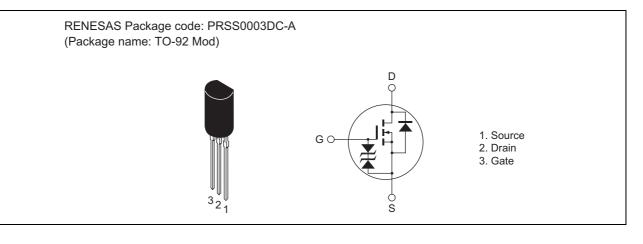
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G1534-0300 Rev.3.00 Feb 01, 2008

# Features

- Capable of 2.5V gate drive
- Low drive current
- Low on-resistance

# Outline



# **Absolute Maximum Ratings**

			$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	250	V
Gate to source voltage	V <sub>GSS</sub>	±10	V
Drain current	I <sub>D</sub> <sup>Note1</sup>	1	А
Drain peak current	Note2 D (pulse)	2	А
Body-drain diode reverse drain current	I <sub>DR</sub>	0.5	А
Body-drain diode reverse drain peak current	Note2 I <sub>DR (pulse)</sub>	2	А
Channel dissipation	Pch	0.9	W
Channel to ambient thermal impedance	$\theta_{ch-a}$	139	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	٥C

Notes: 1.  $PW \leq 10 \ \mu s, \ duty \ cycle \leq 30\%$ 

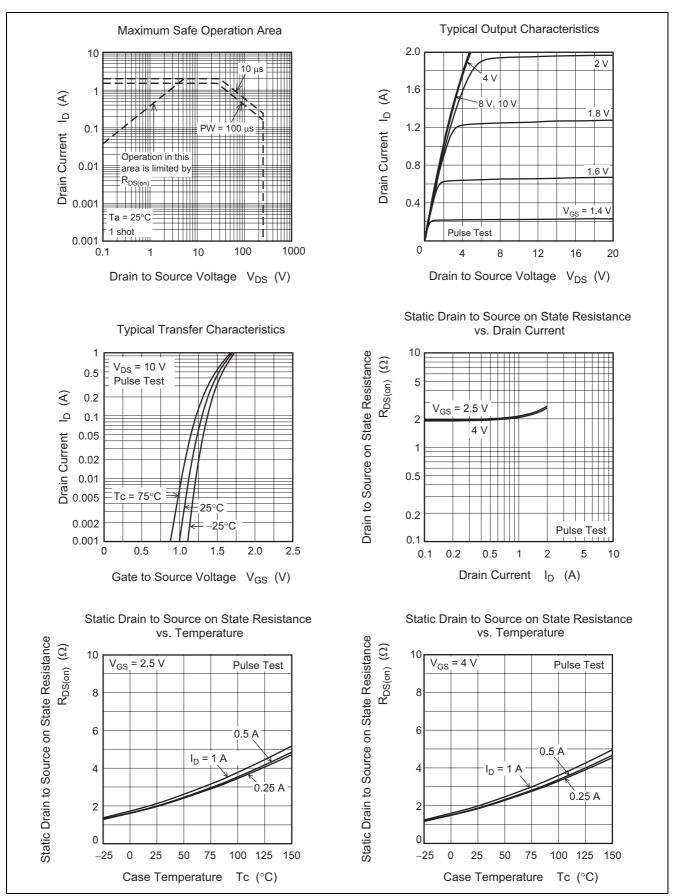
2.  $PW \le 10 \ \mu s$ , duty cycle  $\le 1\%$ 

# **Electrical Characteristics**

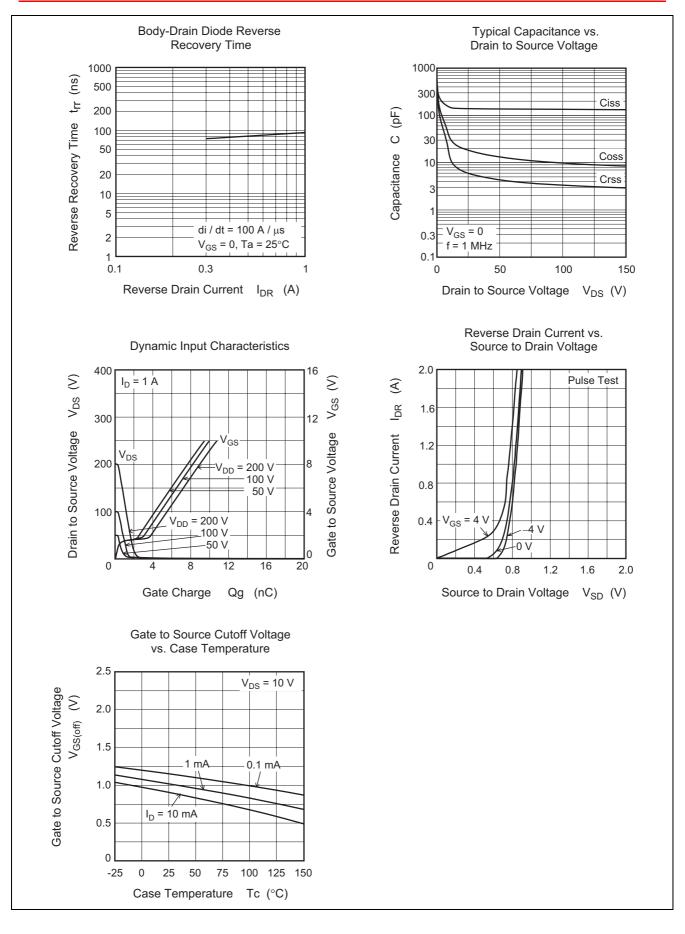
						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	250	—		V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	V <sub>(BR)GSS</sub>	±10	—		V	$I_G = \pm 100 \ \mu A, \ V_{DS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 250 \text{ V}, \text{ V}_{GS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_	_	±10	μΑ	$V_{GS} = \pm 8 \text{ V},  V_{DS} = 0$
Gate to source cutoff voltage	V <sub>GS(off)</sub>	0.5	_	1.5	V	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$
Static drain to source on state resistance	R <sub>DS(on)</sub>	_	1.9	2.6	Ω	$I_D = 0.5 \text{ A}, \text{ V}_{\text{GS}} = 4 \text{ V}^{\text{ Note3}}$
Static drain to source on state resistance	R <sub>DS(on)</sub>	_	2.0	2.7	Ω	$I_D = 0.5 \text{ A}, \text{ V}_{GS} = 2.5 \text{ V}^{Note3}$
Input capacitance	Ciss	_	140		pF	V <sub>DS</sub> = 25 V
Output capacitance	Coss		18		pF	V <sub>GS</sub> = 0 f = 1 MHz
Reverse transfer capacitance	Crss	_	6		pF	
Turn-on delay time	t <sub>d(on)</sub>	_	14		ns	$I_D = 0.5 \text{ A}$ $V_{GS} = 4 \text{ V}$ $R_L = 250 \Omega$ $R_g = 10 \Omega$
Rise time	tr	_	17	—	ns	
Turn-off delay time	t <sub>d(off)</sub>	_	46	_	ns	
Fall time	t <sub>f</sub>	_	16	_	ns	
Total gate charge	Qg	_	5.5	_	nC	$V_{DD} = 200 V$ $V_{GS} = 4 V$ $I_{D} = 1 A$
Gate to source charge	Qgs	_	0.4	_	nC	
Gate to drain charge	Qgd		3.1	_	nC	
Body-drain diode forward voltage	V <sub>DF</sub>		0.78	1.20	V	$I_F = 0.5 \text{ A}, V_{GS} = 0^{Note3}$
Body-drain diode reverse recovery time	t <sub>rr</sub>	_	80	—	ns	$I_{F} = 0.5 \text{ A}, V_{GS} = 0 \\ di_{F}/dt = 100 \text{ A}/\mu \text{s}$

Notes: 3. Pulse test

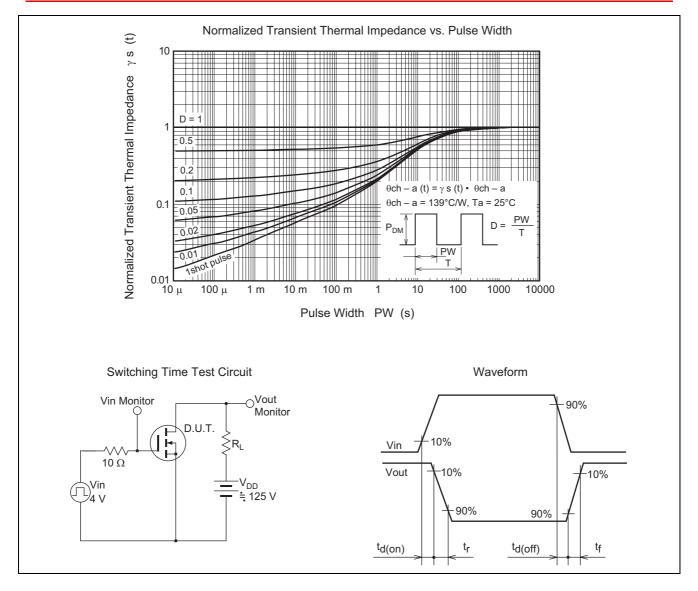
## **Main Characteristics**



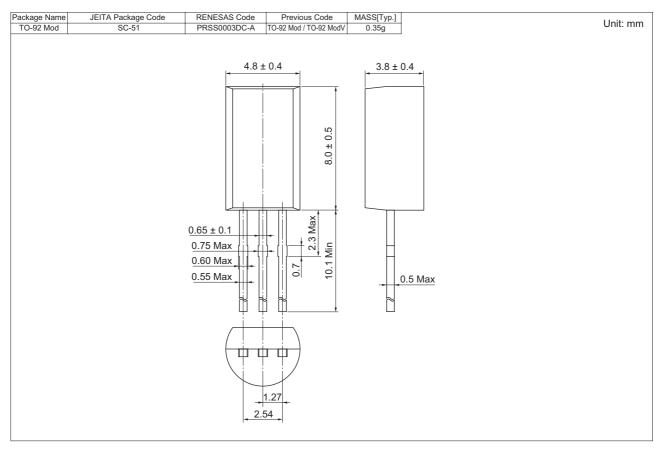
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# **Package Dimensions**



# **Ordering Information**

Part No.	Quantity	Shipping Container
2SK4093TZ-E	2500 pcs	Hold Box, Radial Taping

# RenesasTechnology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

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Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510

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